Quad 3-State Noninverting Buffers

High–Performance Silicon–Gate CMOS

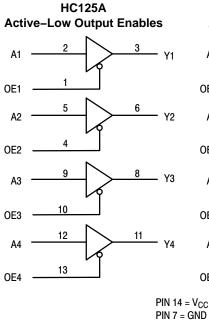
The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

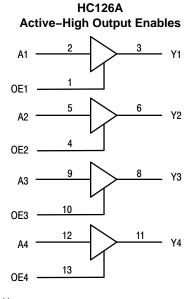
The HC125A and HC126A noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125A) or active-high (HC126A).

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

LOGIC DIAGRAM





ON

ON Semiconductor®

http://onsemi.com



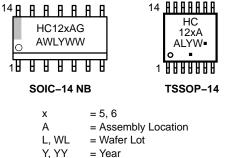
SOIC-14 NB D SUFFIX CASE 751A



PIN ASSIGNMENT

OE1 [1•	14] v _{cc}
A1 [2	13] OE4
Y1 [] A4
0E2 [4	11] Y4
A2 [5	10	OE3
Y2 [6	9] A3
GND [7	8] Y3
			1

MARKING DIAGRAMS



- Y, YY = Year W. WW = Work Week
- G or = = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

	HC125A			HC126A								
Inp	outs	Output		Inputs		Inputs		Inputs		Inputs Ou		Output
Α	OE	Y		Α	OE	Y						
н	L	н		н	н	н						
L	L	L		L	Н	L						
Х	Н	Z		Х	L	Z						

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	–0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V _{CC}	V
T _A	Operating Temperature, All Package Types		-55	+125	°C
t _r , t _f	(Figure 1) V _C	$_{C} = 2.0 V$ $_{C} = 4.5 V$ $_{C} = 6.0 V$	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{cc} v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 V$	2.0	1.5	1.5	1.5	V
		$ I_{out} \le 20 \mu A$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
VIL	Maximum Low-Level Input Voltage	$V_{out} = 0.1 V$	2.0	0.5	0.5	0.5	V
		$ I_{out} \le 20 \mu A$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High–Level Output	$V_{in} = V_{IH}$	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out} \le 20 \mu A$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out} \le 3.6 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V _{OL}	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
	Voltage	$ I_{out} \le 20 \ \mu A$	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out} \le 3.6 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{out} \le 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum Three–State Leakage	Output in High–Impedance State	6.0	±0.5	±5.0	±10	μA
	Current	$V_{in} = V_{IL} \text{ or } V_{IH}$					
		$V_{out} = V_{CC}$ or GND					
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC} \text{ or } GND$	6.0	4.0	40	160	μA
	(per Package)	$I_{out} = 0 \ \mu A$]	

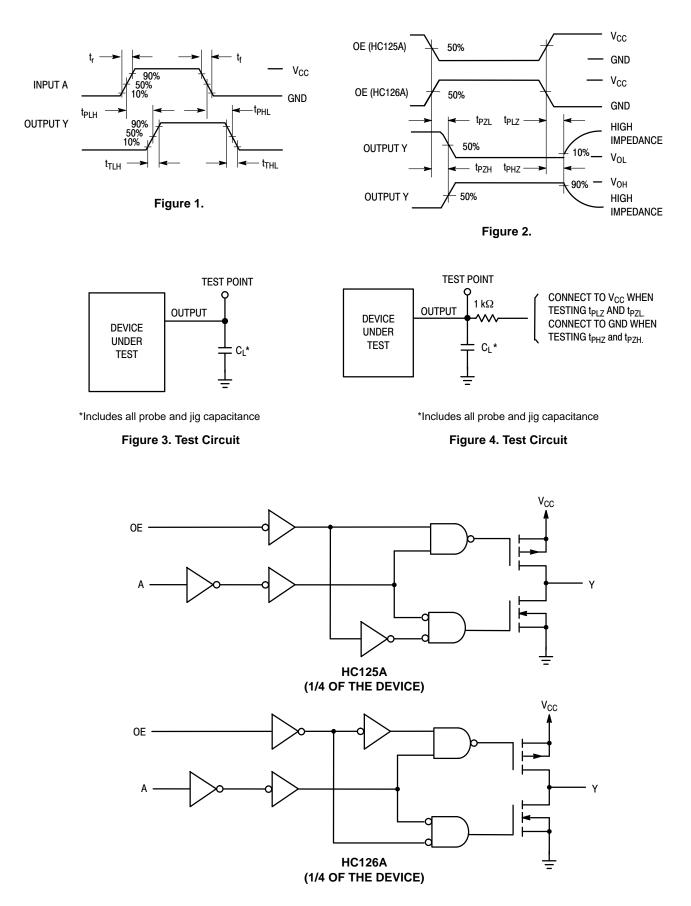
DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Guaranteed Limit		mit	
Symbol	Parameter	v _{cc} v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} ,	Maximum Propagation Delay, Input A to Output Y	2.0	90	115	135	ns
t _{PHL}	(Figures 1 and 3)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t _{PLZ} ,	Maximum Propagation Delay, Output Enable to Y	2.0	120	150	180	ns
t _{PHZ}	(Figures 2 and 4)	3.0	45	60	80	
		4.5	24	30	36	
		6.0	20	26	31	
t _{PZL} ,	Maximum Propagation Delay, Output Enable to Y	2.0	90	115	135	ns
t _{PZH}	(Figures 2 and 4)	3.0	36	45	60	
		4.5	18	23	27	
		6.0	15	20	23	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	60	75	90	ns
t _{THL}	(Figures 1 and 3)	3.0	22	28	34	
		4.5	12	15	18	
		6.0	10	13	15	
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
Cout	Maximum 3-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF
			Typical @ 25°C, V _{CC} = 5.0 V		_C = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Buffer)*			30		pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS



ORDERING INFORMATION

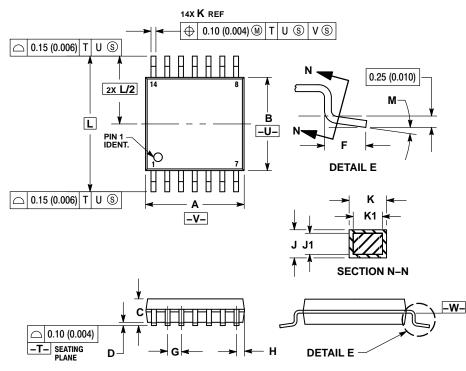
Device	Package	Shipping [†]
MC74HC125ADG	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC74HC125ADR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
MC74HC125ADTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74HC125ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74HC126ADG	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC74HC126ADR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
MC74HC126ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV74HC125ADG*	SOIC-14 NB (Pb-Free)	55 Units / Rail
NLV74HC125ADR2G*	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
NLV74HC125ADTG*	TSSOP-14 (Pb-Free)	55 Units / Rail
NLV74HC125ADTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV74HC126ADR2G*	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
NLV74HC126ADTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE B**



NOTES: 1. DIMENSIONING AND TOLERANCING PER

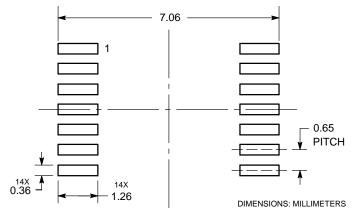
DIMENSIONING AND TOLERANGING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

REFERENCE ONLY.
DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

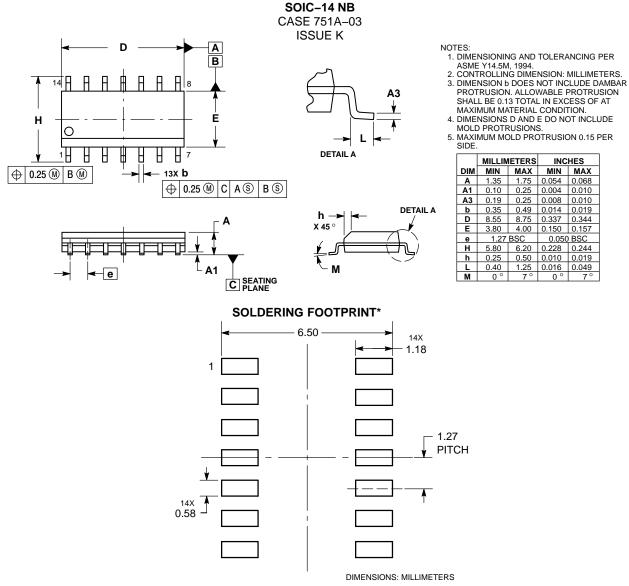
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	0.65 BSC		BSC
н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	40 BSC 0.252 BSC		
Μ	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the use are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any such unintended or unauthorized application. Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manne

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative